	Application No.	cation No. Applicant(s)	
Notice of Allowshility	10/708,504	CHEN, SHIAO-SHIEN	
Notice of Allowability	Examiner	Art Unit	J
	Fazli Erdem	2826	· · · · · · · · · · · · · · · · · · ·
The MAILING DATE of this communication apperature All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED or other appropriate comm GHTS. This application is	in this application. If not include nunication will be mailed in due o	d course. <b>THIS</b>
1. This communication is responsive to <u>03/08/2004</u> .		SUPERVISORY PATERY EXAMINER	
2. The allowed claim(s) is/are <u>1-15</u> .		TECHNOLOGY CENTER 280	00
3. The drawings filed on <u>08 March 2004</u> are accepted by the	Examiner.	14)	
<ul> <li>4. ☐ Acknowledgment is made of a claim for foreign priority una) ☐ All b) ☐ Some* c) ☐ None of the:</li> <li>1. ☐ Certified copies of the priority documents have</li> <li>2. ☐ Certified copies of the priority documents have</li> <li>3. ☐ Copies of the certified copies of the priority documents have International Bureau (PCT Rule 17.2(a)).</li> <li>* Certified copies not received:</li> </ul>	been received. been received in Applicati	on No	ion from the
Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONM THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.		e a reply complying with the req	uirements
5. A SUBSTITUTE OATH OR DECLARATION must be subminification (PTO-152) which give	itted. Note the attached EXes reason(s) why the oath o	AMINER'S AMENDMENT or NO or declaration is deficient.	OTICE OF
6. CORRECTED DRAWINGS ( as "replacement sheets") mus	t be submitted.		
(a) I including changes required by the Notice of Draftspers	on's Patent Drawing Revie	w ( PTO-948) attached	
1) ☐ hereto or 2) ☐ to Paper No./Mail Date			
(b) including changes required by the attached Examiner's Paper No./Mail Date	Amendment / Comment o	or in the Office action of	
Identifying indicia such as the application number (see 37 CFR 1. each sheet. Replacement sheet(s) should be labeled as such in t			back) of
7. DEPOSIT OF and/or INFORMATION about the deposit attached Examiner's comment regarding REQUIREMENT I	SIT OF BIOLOGICAL MAT FOR THE DEPOSIT OF BI	ERIAL must be submitted. N OLOGICAL MATERIAL.	ote the
Attachment(s)  1. ☑ Notice of References Cited (PTO-892)  2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948)  3. ☐ Information Disclosure Statements (PTO-1449 or PTO/SB/0 Paper No./Mail Date  4. ☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material	6. ☐ Interview S Paper No. 8), 7. ☐ Examiner's	nformal Patent Application (PTO Summary (PTO-413), /Mail Date s Amendment/Comment s Statement of Reasons for Allov	·

## **DETAILED ACTION**

## **EXAMINER'S AMENDMENT**

1. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

Authorization for this examiner's amendment was given in a telephone voicemail left by the attorney on December 10, 2004 and email that was sent by the attorney on December 10, 2004.

The application has been amended as follows:

Claim 7 will read: "The ESD protection device of claim 4 further comprising halo implant regions"

Claim 14 will read: "The ESD protection device according to claim 13 further comprising P+ halo implant regions"

## Allowable Subject Matter

- 2. Claims 1-15 allowed.
- 3. The following is an examiner's statement of reasons for allowance: Prior art failed to establish an electrostatic discharge (ESD) protection device with a first MOS transistor, a second MOS transistor and at least one floating gate MOS transistor comprising a floating gate dielectric formed on a substrate of first conductivity type and a floating gate overlying the floating gate dielectric where the floating gate MOS transistor is serially connected to first MOS transistor via

Art Unit: 2826

second heavily doped region that is implanted to substrate and is connected to second d MOS transistor via third heavily doped region that is implanted to substrate.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

## Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Fazli Erdem whose telephone number is (571) 272-1914. The examiner can normally be reached on M - F 8:00 - 5:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nathan Flynn can be reached on (571) 272-1915. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

FE

December 10, 2004